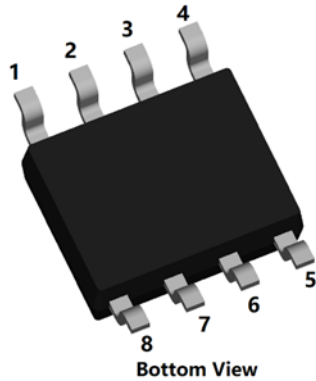
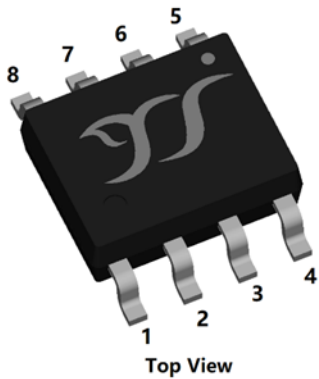
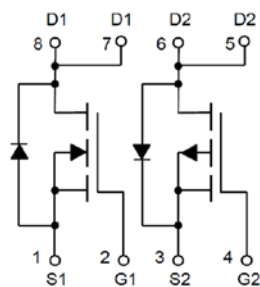


N-Channel and P-Channel Complementary MOSFET



SOP-8



Product Summary

NMOS

• V_{DS}	30V
• I_D	7A
• $R_{DS(ON)}$ (at $V_{GS}=10V$)	<18m Ω
• $R_{DS(ON)}$ (at $V_{GS}=4.5V$)	<30m Ω

PMOS

• V_{DS}	-30V
• I_D	-5A
• $R_{DS(ON)}$ (at $V_{GS}=-10V$)	<43m Ω
• $R_{DS(ON)}$ (at $V_{GS}=-4.5V$)	<63m Ω

General Description

- Trench Power LV MOSFET technology
- High density cell design for low $R_{DS(ON)}$
- High Speed switching
- Moisture Sensitivity Level 3
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

Applications

- Wireless charger
- Load switch
- Power management

■ Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	NMOS	PMOS	Unit
Drain-source Voltage		V_{DS}	30	-30	V
Gate-source Voltage		V_{GS}	± 20	± 20	V
Drain Current	$T_A=25^\circ\text{C}$	I_D	7	-5	A
	$T_A=100^\circ\text{C}$		4.4	-3	
Pulsed Drain Current ^A		I_{DM}	60	-40	A
Total Power Dissipation ^B	$T_A=25^\circ\text{C}$	P_D	2	2	W
	$T_A=100^\circ\text{C}$		0.8	0.8	
Junction and Storage Temperature Range		T_J, T_{STG}	-55~+150	-55~+150	$^\circ\text{C}$

■ Thermal resistance

Parameter	Symbol	NMOS		PMOS		Units	
		Typ	Max	Typ	Max		
Thermal Resistance Junction-to-Ambient ^C	Steady-State	$R_{\theta JA}$	50	60	50	60	$^\circ\text{C/W}$

■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJS4606B	F2	4606B	4000	8000	64000	13" reel



YJS4606B

■ NMOS Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	30	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=30V, V_{GS}=0V$	-	-	1	μA
		$V_{DS}=30V, V_{GS}=0V, T_J=150^\circ\text{C}$	-	-	100	
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0	1.5	2.2	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=7A$	-	15	18	m Ω
		$V_{GS}=4.5V, I_D=5A$	-	23	30	
Diode Forward Voltage	V_{SD}	$I_S=7A, V_{GS}=0V$	-	-	1.2	V
Gate resistance	R_G	$f=1\text{MHz}$	-	2	-	Ω
Maximum Body-Diode Continuous Current	I_S		-	-	7	A
Dynamic Parameters						
Input Capacitance	C_{iss}	$V_{DS}=15V, V_{GS}=0V, f=1\text{MHz}$	-	380	-	pF
Output Capacitance	C_{oss}		-	75	-	
Reverse Transfer Capacitance	C_{rss}		-	60	-	
Switching Parameters						
Total Gate Charge	Q_g	$V_{GS}=10V, V_{DS}=15V, I_D=7A$	-	12.5	-	nC
Gate-Source Charge	Q_{gs}		-	2.5	-	
Gate-Drain Charge	Q_{gd}		-	2.5	-	
Reverse Recovery Charge	Q_{rr}	$I_F=7A, di/dt=100A/\mu s$	-	1.5	-	nC
Reverse Recovery Time	t_{rr}		-	16	-	ns
Turn-on Delay Time	$t_{D(on)}$	$V_{GS}=10V, V_{DD}=15V, I_D=7A$ $R_{GEN}=3\Omega$	-	5	-	ns
Turn-on Rise Time	t_r		-	30	-	
Turn-off Delay Time	$t_{D(off)}$		-	15	-	
Turn-off fall Time	t_f		-	20	-	



YJS4606B

■ PMOS Electrical Characteristics (T_J=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D =-250μA	-30	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-30V, V _{GS} =0V	-	-	-1	μA
		V _{DS} =-30V, V _{GS} =0V, T _J =150°C	-	-	-100	
Gate-Body Leakage Current	I _{GSS}	V _{GS} = ±20V, V _{DS} =0V	-	-	±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D =-250μA	-1.0	-1.5	-2.4	V
Static Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =-10V, I _D =-5A	-	34	43	mΩ
		V _{GS} =-4.5V, I _D =-3.5A	-	49	63	
Diode Forward Voltage	V _{SD}	I _S =-5A, V _{GS} =0V	-	-	-1.2	V
Gate resistance	R _G	f=1MHz	-	15	-	Ω
Maximum Body-Diode Continuous Current	I _S		-	-	-5	A
Dynamic Parameters						
Input Capacitance	C _{iss}	V _{DS} =-15V, V _{GS} =0V, f=1MHz	-	490	-	pF
Output Capacitance	C _{oss}		-	75	-	
Reverse Transfer Capacitance	C _{rss}		-	60	-	
Switching Parameters						
Total Gate Charge	Q _g	V _{GS} =-10V, V _{DS} =-15V, I _D =-5A	-	9	-	nC
Gate-Source Charge	Q _{gs}		-	1.5	-	
Gate-Drain Charge	Q _{gd}		-	2.3	-	
Reverse Recovery Charge	Q _{rr}	I _F =-5A, di/dt=100A/us	-	12	-	nC
Reverse Recovery Time	t _{rr}		-	32	-	ns
Turn-on Delay Time	t _{D(on)}	V _{GS} =-10V, V _{DD} =-15V, I _D =-5A R _{GEN} =2.5Ω	-	9	-	ns
Turn-on Rise Time	t _r		-	3	-	
Turn-off Delay Time	t _{D(off)}		-	29	-	
Turn-off fall Time	t _f		-	15	-	

A. Repetitive rating; pulse width limited by max. junction temperature.

B. P_d is based on max. junction temperature, using junction-case thermal resistance.

C. The value of R_{θJA} is measured with the device mounted on 1 in² FR-4 board with 2oz. Copper, in the still air environment with T_A=25°C. The maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design.



■ NMOS Typical Electrical and Thermal Characteristics Diagrams

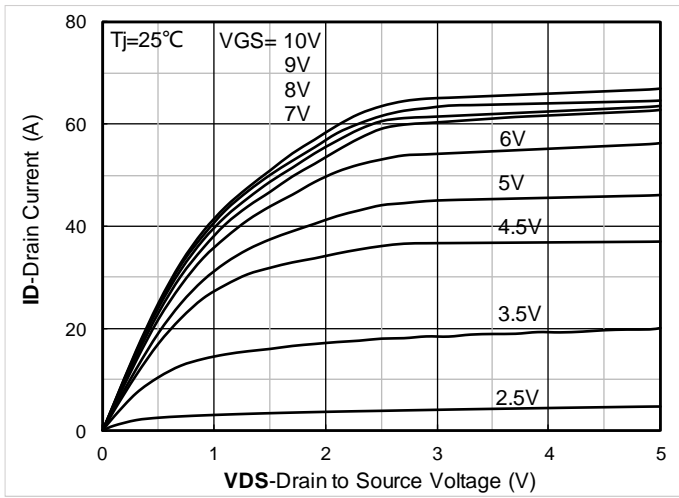


Figure 1. Output Characteristics

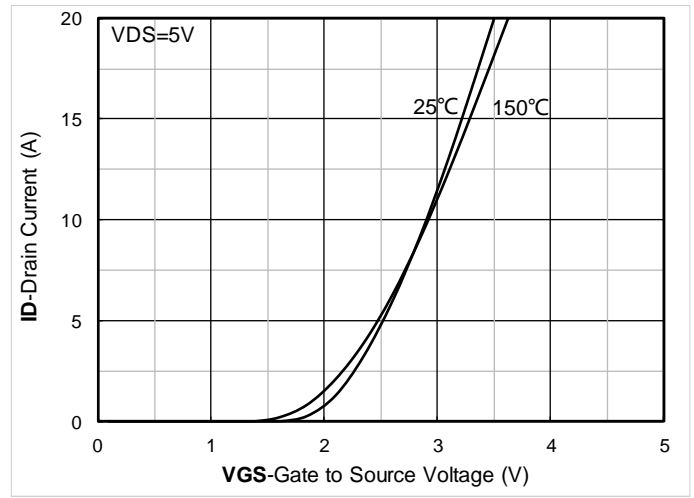


Figure 2. Transfer Characteristics

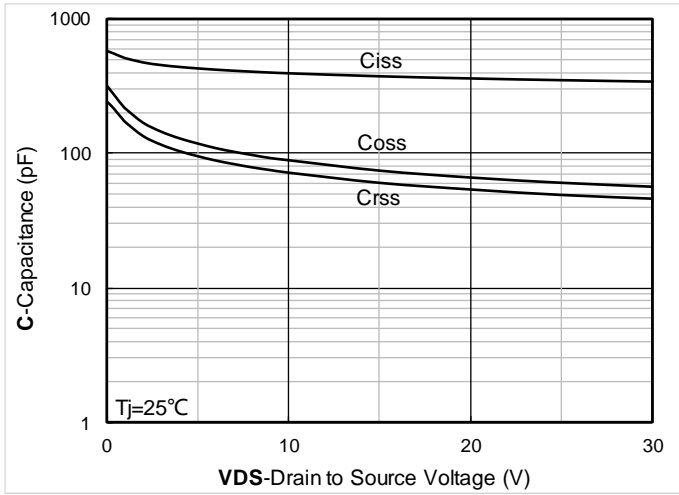


Figure 3. Capacitance Characteristics

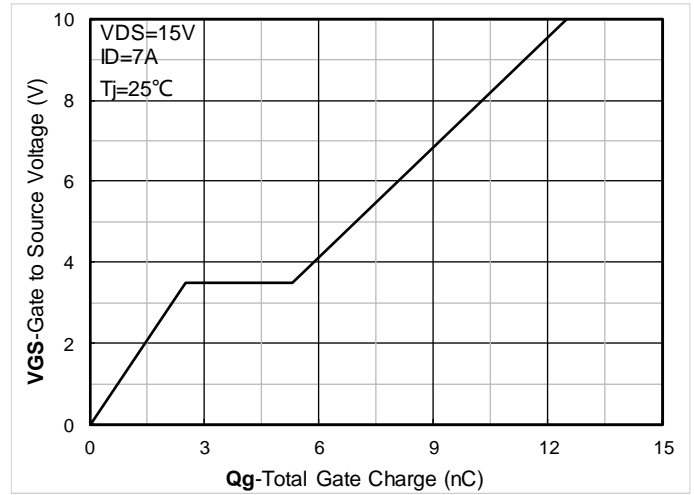


Figure 4. Gate Charge

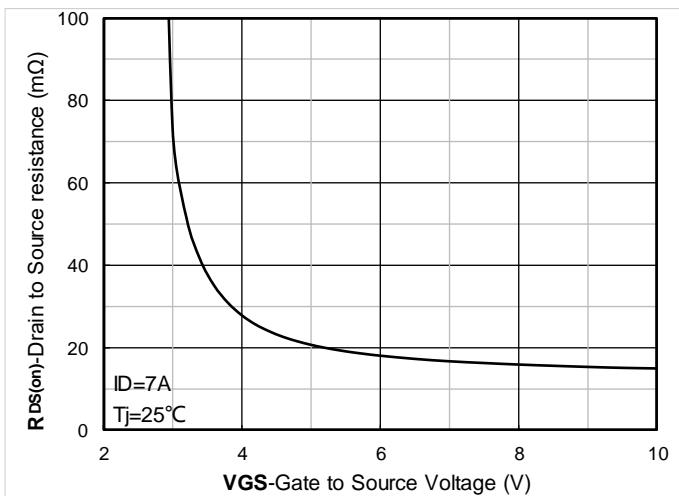


Figure 5. On-Resistance vs Gate to Source Voltage

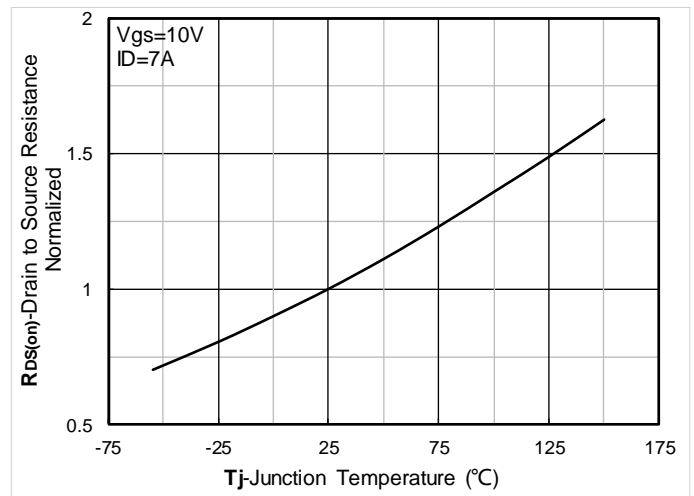


Figure 6. Normalized On-Resistance

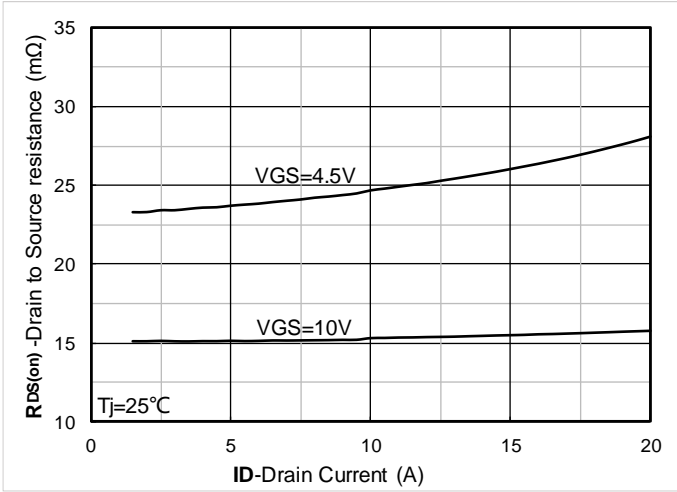


Figure 7. $R_{DS(on)}$ VS Drain Current

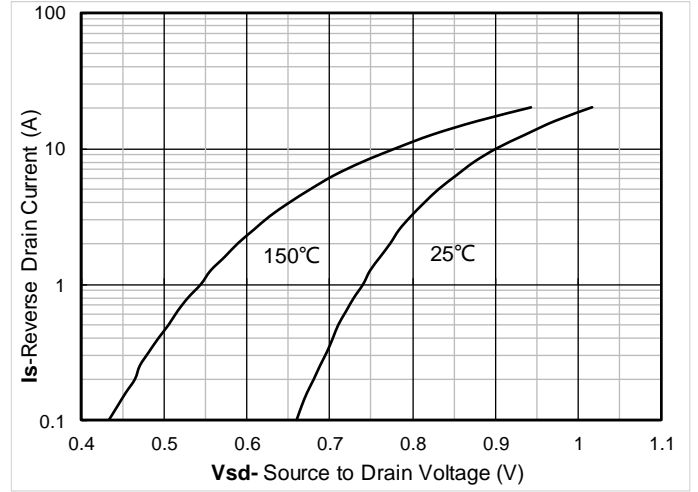


Figure 8. Forward characteristics of reverse diode

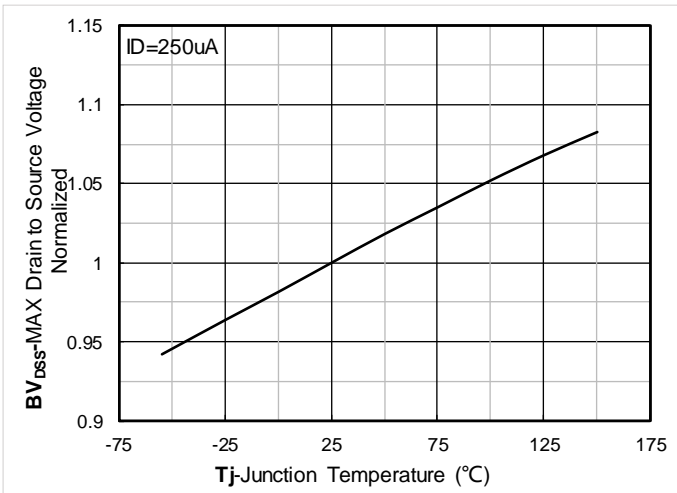


Figure 9. Normalized breakdown voltage

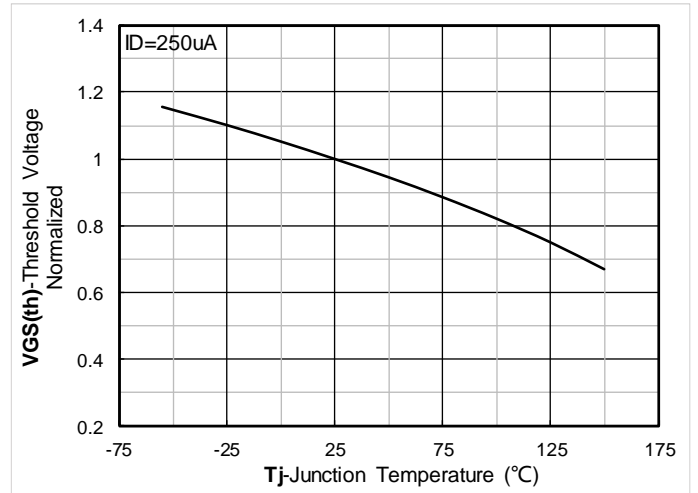


Figure 10. Normalized Threshold voltage

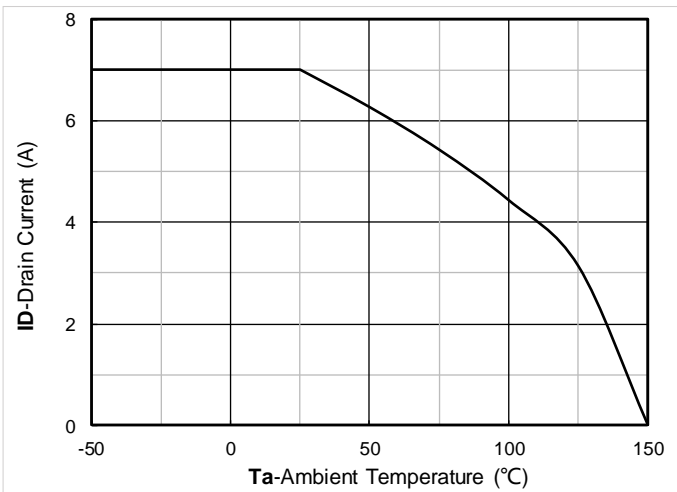


Figure 11. Current dissipation

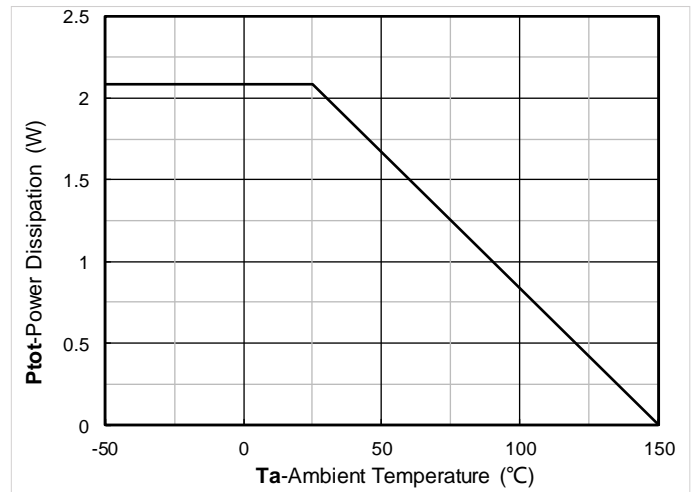


Figure 12. Power dissipation

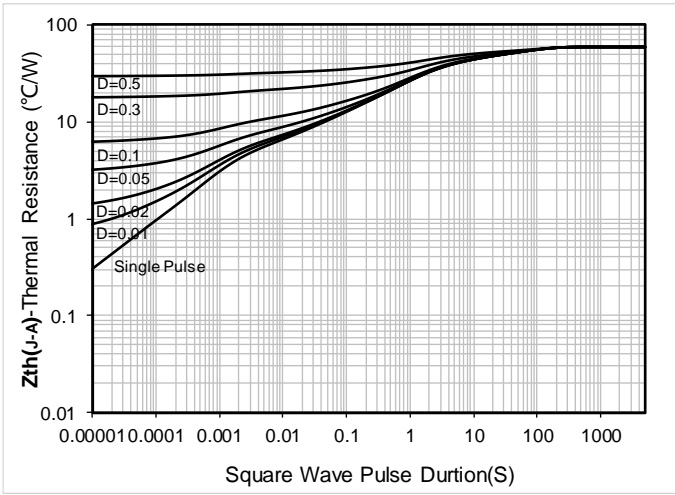


Figure 13. Maximum Transient Thermal Impedance

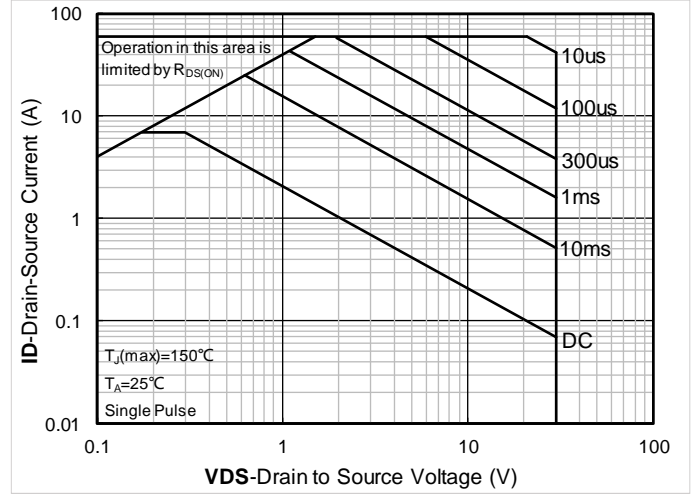


Figure 14. Safe Operation Area

■ PMOS Typical Electrical and Thermal Characteristics Diagrams

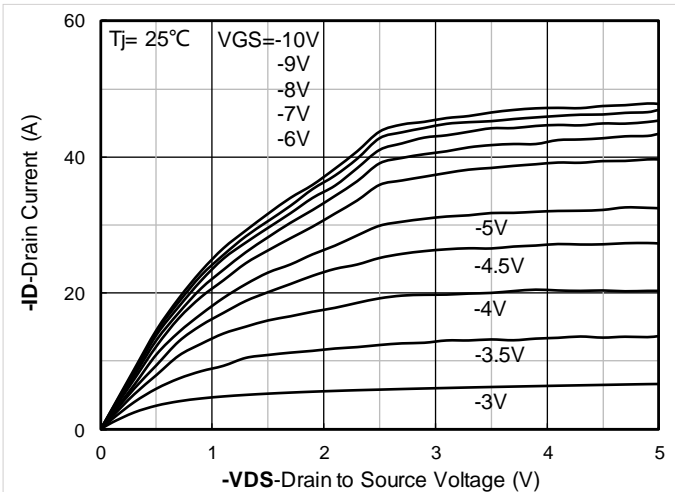


Figure 1. Output Characteristics

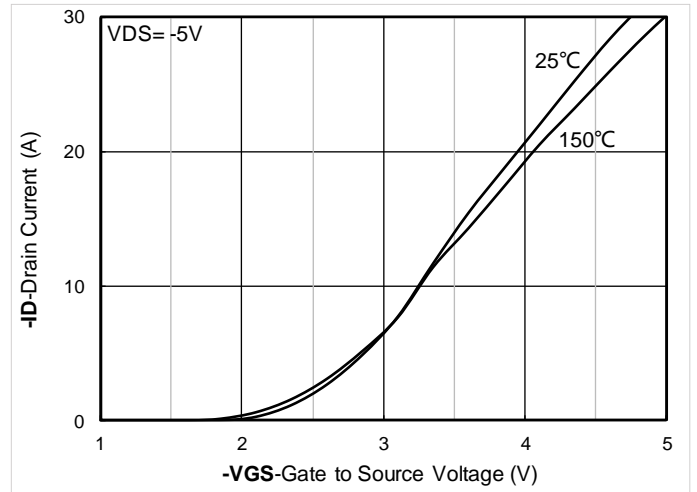


Figure 2. Transfer Characteristics

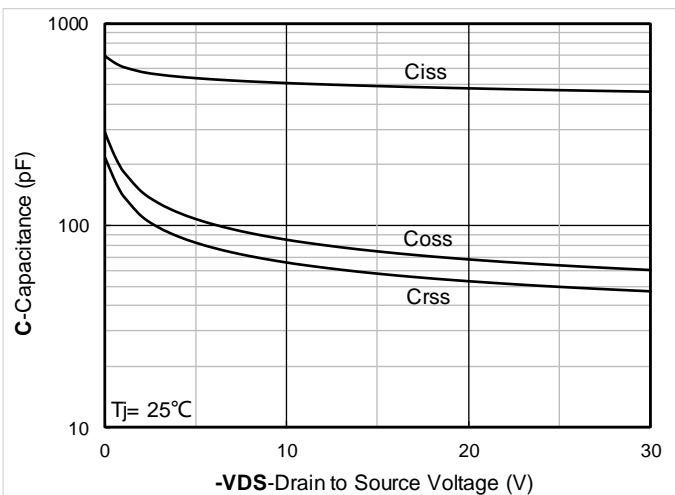


Figure 3. Capacitance Characteristics

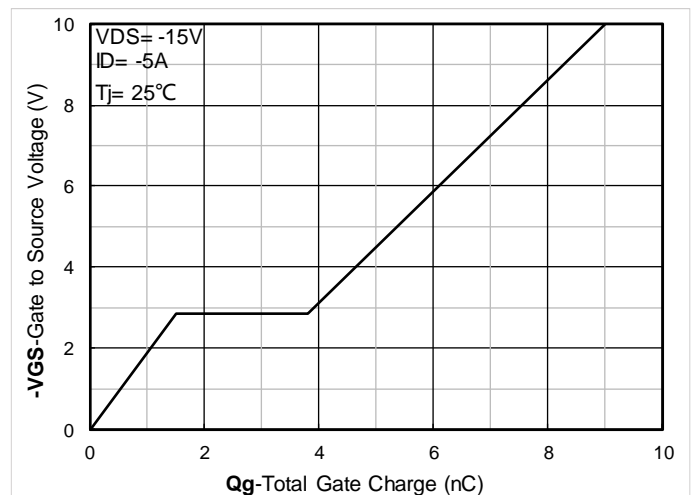


Figure 4. Gate Charge

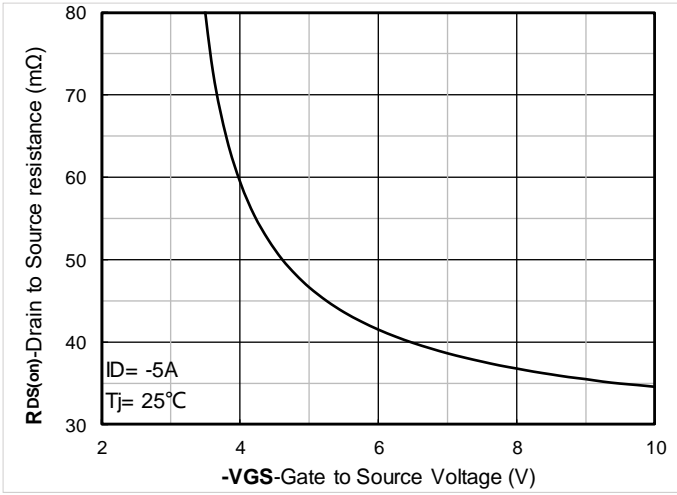


Figure 5. On-Resistance vs Gate to Source Voltage

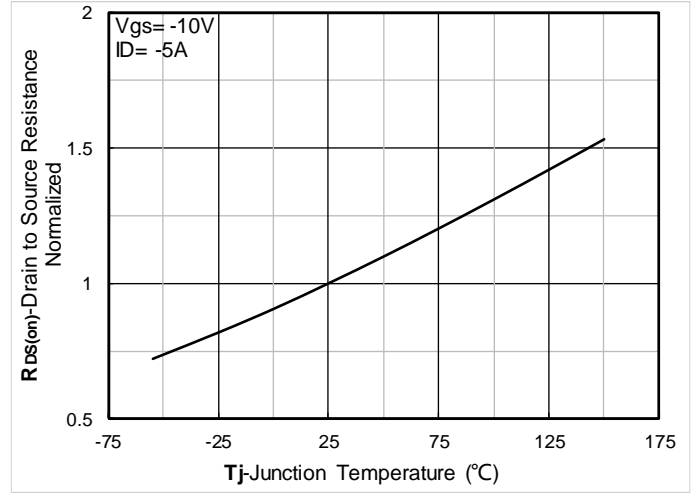


Figure 6. Normalized On-Resistance

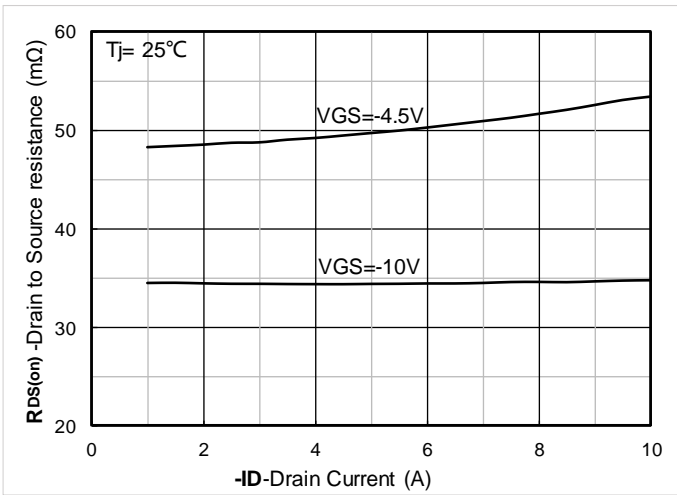


Figure 7. RDS(on) VS Drain Current

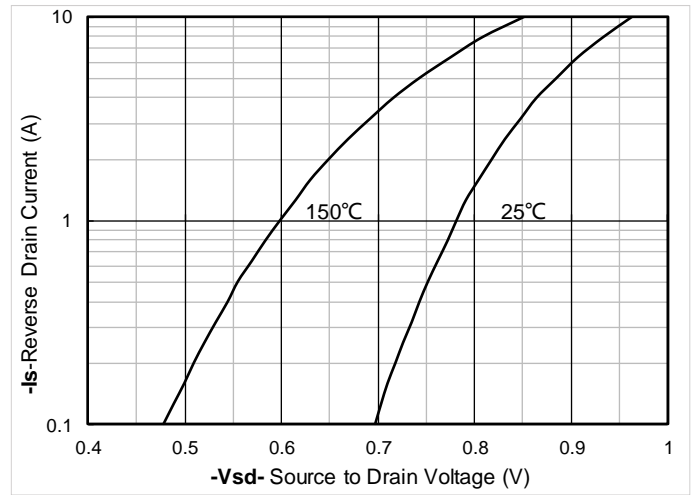


Figure 8. Forward characteristics of reverse diode

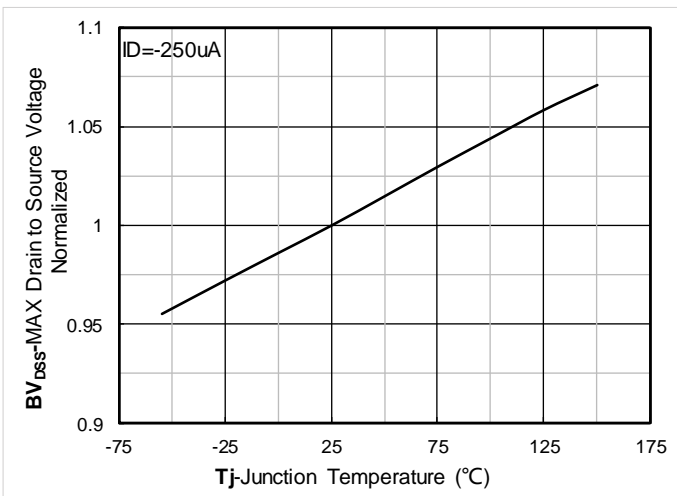


Figure 9. Normalized breakdown voltage

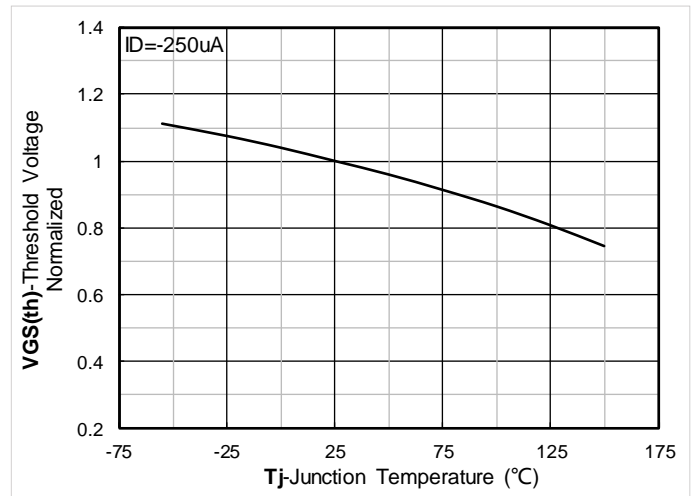


Figure 10. Normalized Threshold voltage

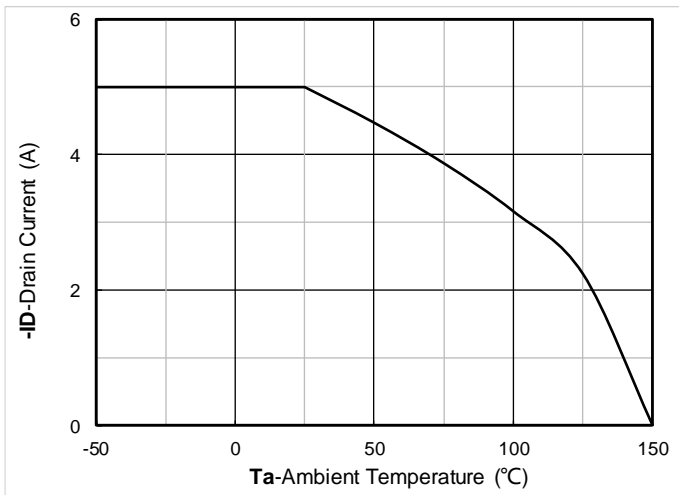


Figure 11. Current dissipation

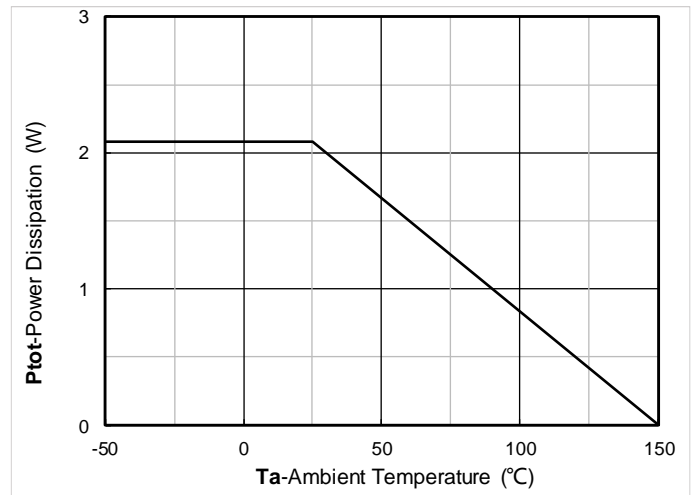


Figure 12. Power dissipation

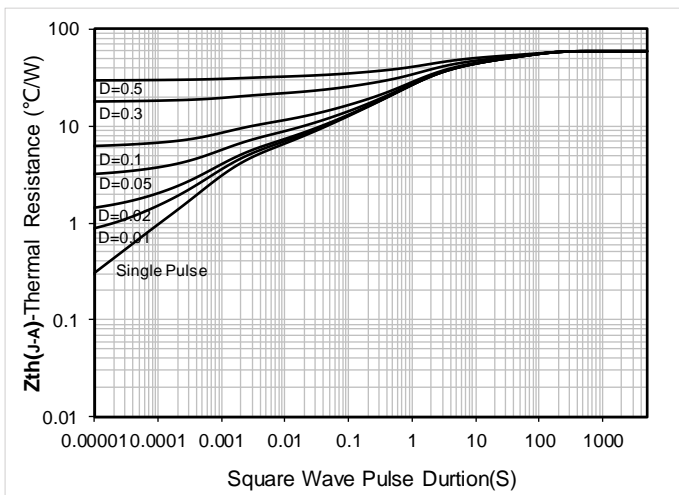


Figure 13. Maximum Transient Thermal Impedance

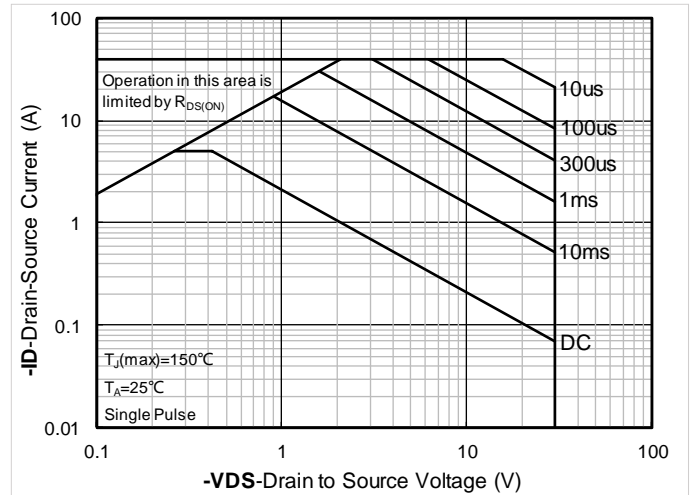
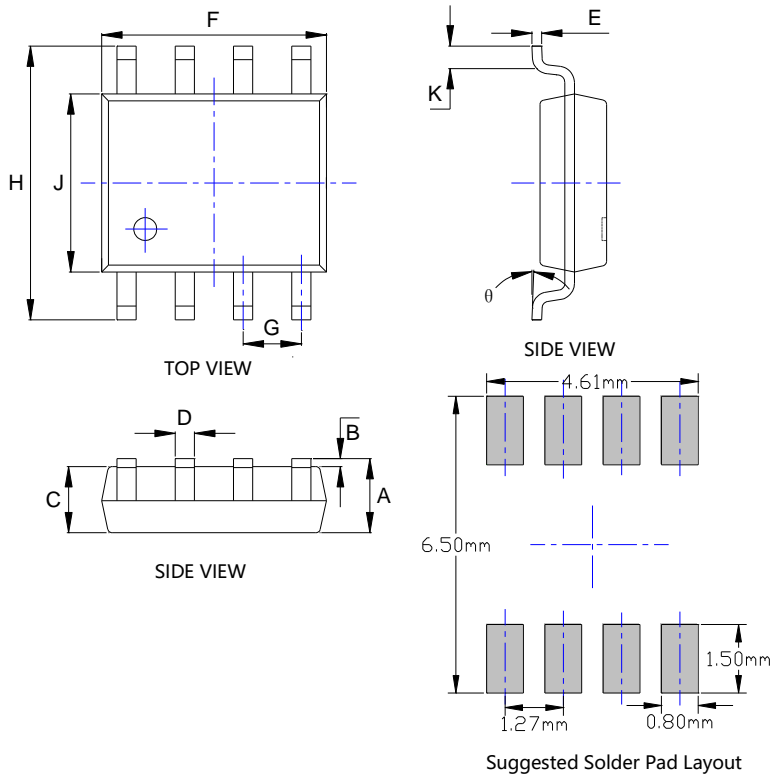


Figure 14. Safe Operation Area

■ SOP-8 Package information



SYMBOL	DIMENSIONS			
	INCHES		Millimeter	
	MIN.	MAX.	MIN.	MAX.
A	0.053	0.069	1.350	1.750
B	0.004	0.010	0.100	0.250
C	0.053	0.061	1.350	1.550
D	0.013	0.020	0.330	0.510
E	0.007	0.010	0.170	0.250
F	0.189	0.197	4.800	5.000
G	0.050BSC		1.270BSC	
H	0.228	0.244	5.800	6.200
J	0.150	0.157	3.800	4.000
K	0.016	0.050	0.400	1.270
θ	0°	8°	0°	8°

Note:

1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.



YJS4606B

Disclaimer

The information presented in this document is for reference only. Yangzhou Yangjie Electronic Technology Co., Ltd. reserves the right to make changes without notice for the specification of the products displayed herein to improve reliability, function or design or otherwise.

The product listed herein is designed to be used with ordinary electronic equipment or devices, and not designed to be used with equipment or devices which require high level of reliability and the malfunction of which would directly endanger human life (such as medical instruments, transportation equipment, aerospace machinery, nuclear-reactor controllers, fuel controllers and other safety devices), Yangjie or anyone on its behalf, assumes no responsibility or liability for any damages resulting from such improper use of sale.

This publication supersedes & replaces all information previously supplied. For additional information, please visit our website <http://www.21yangjie.com> , or consult your nearest Yangjie's sales office for further assistance.